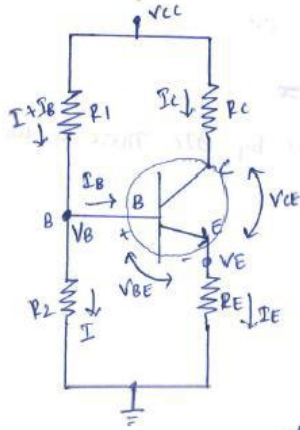




Topic 1.5 : Voltage divider bias configuration

3. Voltage Divider Bias / Self Bias / potential divider Bias



- * The biasing is provided by R_1, R_2 & R_E .
- * The resistors R_1 & R_2 act as a potential divider giving a fixed voltage to point B i.e. base.
- * If I_C increases due to change in temperature or β , the I_E also increases & the voltage drop across R_E increases, decreasing the V_{BE} .
- * Due to reduction in V_{BE} , I_B & I_C also reduced.
- * \therefore We can say that negative feedback exist in the emitter bias circuit.

- * The voltage across R_2 is the base voltage V_B .
- * Apply voltage divider theorem to find V_B we get

$$V_B = \frac{R_2(I)}{R_1(I+I_B)+R_2(I)} \times V_{CC}$$

$\therefore I \gg I_B$ so we can omit $I+I_B$

So

$$V_B = \frac{R_2}{R_1+R_2} V_{CC}$$

- * The voltage across R_E is V_E

$$V_E = I_E R_E = V_B - V_{BE}$$

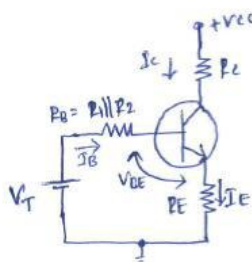
$$\therefore I_E = \frac{V_B - V_{BE}}{R_E}$$

- * Apply KVL to the collector-emitter circuit we get

$$V_{CC} - I_C R_C - V_{CE} - I_E R_E = 0$$

$$\therefore V_{CE} = V_{CC} - I_C R_C - I_E R_E$$

Modified circuit



Thevenin's equivalent circuit

- * Here, R_1 & R_2 are replaced by R_B & V_T , where R_B is the parallel combination of R_1 & R_2 & V_T is the Thevenin's Voltage.

- * R_B is calculated as $R_B = \frac{R_1 R_2}{R_1 + R_2}$



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* Apply KVL to the Base-Emitter junction

$$V_T = I_B R_B + V_{BE} + I_E R_E$$

$$= I_B R_B + V_{BE} + (I_C + I_B) R_E$$

$$= I_B R_B + V_{BE} + I_C R_E + I_B R_E$$

$$V_T = I_B (R_B + R_E) + V_{BE} + I_C R_E$$

$$V_{BE} = V_T - I_B (R_B + R_E) - I_C R_E$$

Stability Factors

* Here the Thevenin's voltage V_T is given by

$$V_T = \frac{R_2 V_{cc}}{R_1 + R_2} \quad \& \ R_1 \& R_2 \text{ replaced by } R_B$$

* Apply KVL to the base-emitter junction

$$V_T = I_B R_B + V_{BE} + (I_B + I_C) R_E \quad \text{--- (1)}$$

* differentiate eqn (1) w.r. to I_C & V_{BE} to be independent of I_C
we get-

$$0 = \frac{\partial I_B}{\partial I_C} R_B + 0 + \frac{\partial I_B}{\partial I_C} R_E + \frac{\partial I_C}{\partial I_C} R_E$$

$$0 = \frac{\partial I_B}{\partial I_C} (R_B + R_E) + R_E$$

$$\frac{\partial I_B}{\partial I_C} = \frac{-R_E}{R_B + R_E} \quad \text{--- (2)}$$

* W.K.T

$$S = \frac{1 + \beta}{1 - \beta \left(\frac{\partial I_B}{\partial I_C} \right)} = \frac{1 + \beta}{1 - \beta \left(\frac{-R_E}{R_B + R_E} \right)} = \frac{1 + \beta}{1 + \beta \left(\frac{R_E}{R_B + R_E} \right)}$$

* Take LCM

$$S = \frac{(1 + \beta)(R_B + R_E)}{R_B + R_E + \beta R_E} = \frac{(1 + \beta)(R_B + R_E)}{R_B + (1 + \beta)R_E}$$

* Dividing each term by R_E we get

$$S = \frac{(1 + \beta) \left(\frac{R_B}{R_E} + \frac{R_E}{R_E} \right)}{\frac{R_B}{R_E} + (1 + \beta) \frac{R_E}{R_E}} = \frac{(1 + \beta) \left(1 + \frac{R_B}{R_E} \right)}{(1 + \beta) + \frac{R_B}{R_E}}$$



* The ratio R_B/R_E controls value of stability factor S .

* If $R_B/R_E \ll 1$ then $S = \frac{1+\beta}{1+\beta} = 1$

S'

$$S' = \frac{\partial I_C}{\partial V_{BE}} \Big|_{I_{CQ} + \beta \text{ constant}}$$

* W.K.T

$$I_C = (1+\beta)I_{CQ} + \beta I_B \quad \text{--- (1)}$$

$$V_T = I_B R_B + V_{BE} + (I_B + I_C) R_E \quad \text{--- (2)}$$

$$V_{BE} = V_T - (R_E + R_B) I_B - R_E I_C \quad \text{--- (3)}$$

* By rewriting the eqn (1) in terms of I_B

$$I_B = \frac{I_C - (1+\beta)I_{CQ}}{\beta} \quad \text{--- (4)}$$

* Substitute I_B in eqn (3) we get

$$\begin{aligned} \text{(3) } V_{BE} &= V_T - (R_E + R_B) I_B - R_E I_C \\ &= V_T - (R_E + R_B) \left[\frac{I_C - (1+\beta)I_{CQ}}{\beta} \right] - R_E I_C \\ &= V_T - \frac{(R_E + R_B) I_C}{\beta} + \frac{(R_E + R_B)(1+\beta)I_{CQ}}{\beta} - R_E I_C \end{aligned}$$

* Take the common term's Outside

$$V_{BE} = V_T - \left[\frac{(1+\beta)R_E + R_B}{\beta} \right] I_C + \frac{(R_E + R_B)(1+\beta)I_{CQ}}{\beta} \quad \text{--- (5)}$$

* differentiate eqn (5) w.r.t V_{BE}

$$\begin{aligned} \frac{\partial V_{BE}}{\partial V_{BE}} &= 0 - \left(\frac{(1+\beta)R_E + R_B}{\beta} \right) \frac{\partial I_C}{\partial V_{BE}} + 0 \\ \downarrow 1 \\ \frac{\partial I_C}{\partial V_{BE}} &= \frac{-\beta}{R_B + (1+\beta)R_E} \end{aligned}$$

$$S' = \frac{-\beta}{R_B + (1+\beta)R_E}$$

S'' :

$$S'' = \frac{\partial I_C}{\partial \beta} \Big|_{I_{CQ} + V_{BE} \text{ as constants}}$$



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$$V_{BE} = V_T - \frac{(R_B + (1+\beta)R_E)I_C}{\beta} + \left[\frac{(R_E + R_B)(1+\beta)}{\beta} \right] I_{CQ}$$
$$= V_T - \frac{[R_B + (1+\beta)R_E]I_C}{\beta} + V' - 0$$

* We can rewrite the eqn (6) in terms of I_C

$$\frac{[R_B + (1+\beta)R_E]I_C}{\beta} = V_T - V' - V_{BE}$$

$$I_C = \frac{(V_T - V' - V_{BE})\beta}{R_B + (1+\beta)R_E} \quad \text{--- (7) } \Rightarrow \quad \frac{u}{v} \text{ format}$$

$\hookrightarrow \frac{v du - u dv}{v^2}$

* Differentiating eqn (7) w.r.t. β

$$\frac{\partial I_C}{\partial \beta} = \frac{R_B + (1+\beta)R_E (V_T - V' - V_{BE}) - \beta (V_T - V' - V_{BE}) R_E}{(R_B + (1+\beta)R_E)^2}$$

* Multiply numerator & denominator by $(1+\beta)$ & β

$$= \frac{(1+\beta)(R_B + R_E)(V_T - V' - V_{BE})\beta}{\beta(1+\beta)[R_B + R_E(1+\beta)][R_B + R_E(1+\beta)]}$$

$\downarrow \qquad \qquad \qquad \downarrow$
 $S \qquad \qquad \qquad I_C$

$$\frac{\partial I_C}{\partial \beta} = \frac{S}{\beta(1+\beta)} \times I_C$$

$$S'' = \frac{I_C S}{\beta(1+\beta)}$$

Advantages

* The stability factor S for voltage divider bias is less as compared to another biasing circuit

* So this circuit is more stable & hence it's most commonly used.



Load line Analysis for voltage divider bias

- * Apply KVL to the collector-emitter circuit

$$V_{CC} - I_C R_C - V_{CE} - I_E R_E = 0$$

- * Assume $I_E \approx I_C$

$$V_{CC} - I_C (R_C + R_E) - V_{CE} = 0$$

$$I_C = -\frac{1}{R_C + R_E} V_{CE} + \frac{V_{CC}}{R_C + R_E}$$

- * This equation represents the dc load line with slope of $-\frac{1}{R_C + R_E}$ & y-intercept of $\frac{V_{CC}}{R_C + R_E}$

- * When $I_C = 0$ i.e. the transistor is in cut-off region
 $V_{CE} = V_{CC}$

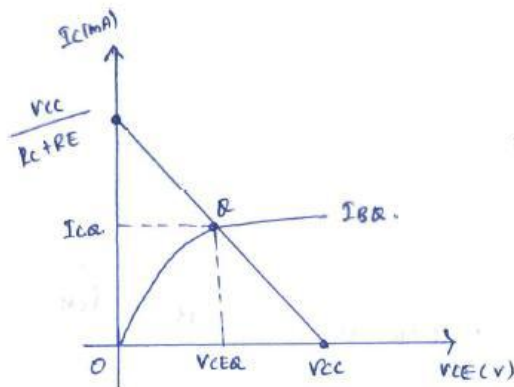
- * When $V_{CE} = 0$ i.e. the transistor is in saturation region

$$I_C = \frac{V_{CC}}{R_C + R_E}$$

- * Thus the 2 end points are $(V_{CC}, 0)$ & $(0, \frac{V_{CC}}{R_C + R_E})$ By joining these 2 end points, a dc load line is drawn.

- * From the base-emitter circuit

$$I_B = \frac{V_B - V_{BE}}{R_B + (1 + \beta) R_E}$$



- * The saturation current for the circuit

$$I_{C, \text{sat}} = \frac{V_{CC}}{R_C + R_E}$$